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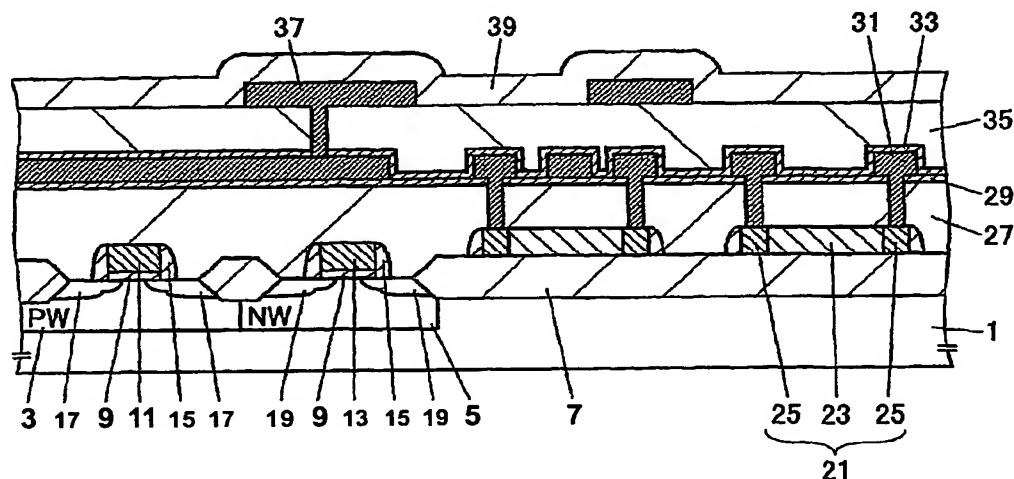
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(54) Title: SEMICONDUCTOR DEVICE AND FABRICATION PROCESS THEREOF



(57) Abstract: A semiconductor device includes a semiconductor substrate, a polysilicon pattern formed on the semiconductor substrate via an insulation film, an interlayer insulation film formed on the semiconductor substrate so as to cover the polysilicon pattern, and a metal interconnection layer pattern formed on the interlayer insulation film, wherein the metal interconnection layer pattern carrying silicon nitride films respectively on a top surface, a bottom surface and sidewall surfaces thereof.

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